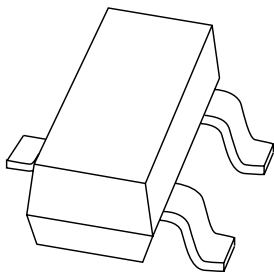


DATA SHEET



BF570

NPN medium frequency transistor

Product data sheet
Supersedes data of 2004 Jan 13

2004 Mar 15

NPN medium frequency transistor

BF570

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 15 V)
- Low feedback capacitance (max. 2.2 pF).

APPLICATIONS

- Monitors
- Battery equipped applications.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BF570	61* or B26

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

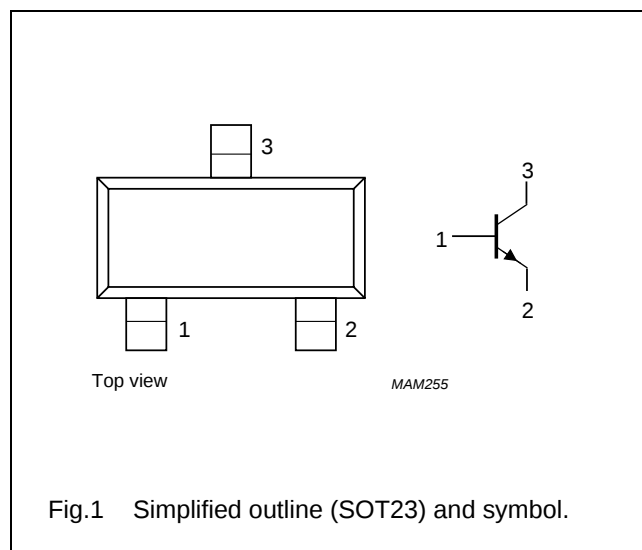


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF570	—	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	40	V
V_{CEO}	collector-emitter voltage	open base	—	15	V
I_{CM}	peak collector current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	—	250	mW
h_{FE}	DC current gain	$I_C = 10\text{ mA}$; $V_{CE} = 1\text{ V}$	40	—	
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$	490	—	MHz

NPN medium frequency transistor

BF570

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	4.5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	500	K/W

CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0\text{ A}; V_{CB} = 20\text{ V}$	–	–	400	nA
		$I_E = 0\text{ A}; V_{CB} = 20\text{ V}; T_j = 125\text{ °C}$	–	–	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0\text{ A}; V_{EB} = 2\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$	40	–	–	
C_{re}	feedback capacitance	$I_C = 0\text{ A}; V_{CE} = 10\text{ V}; f = 1\text{ MHz}$	–	1.6	2.2	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	500	–	–	MHz
		$I_C = 40\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	490	–	–	MHz

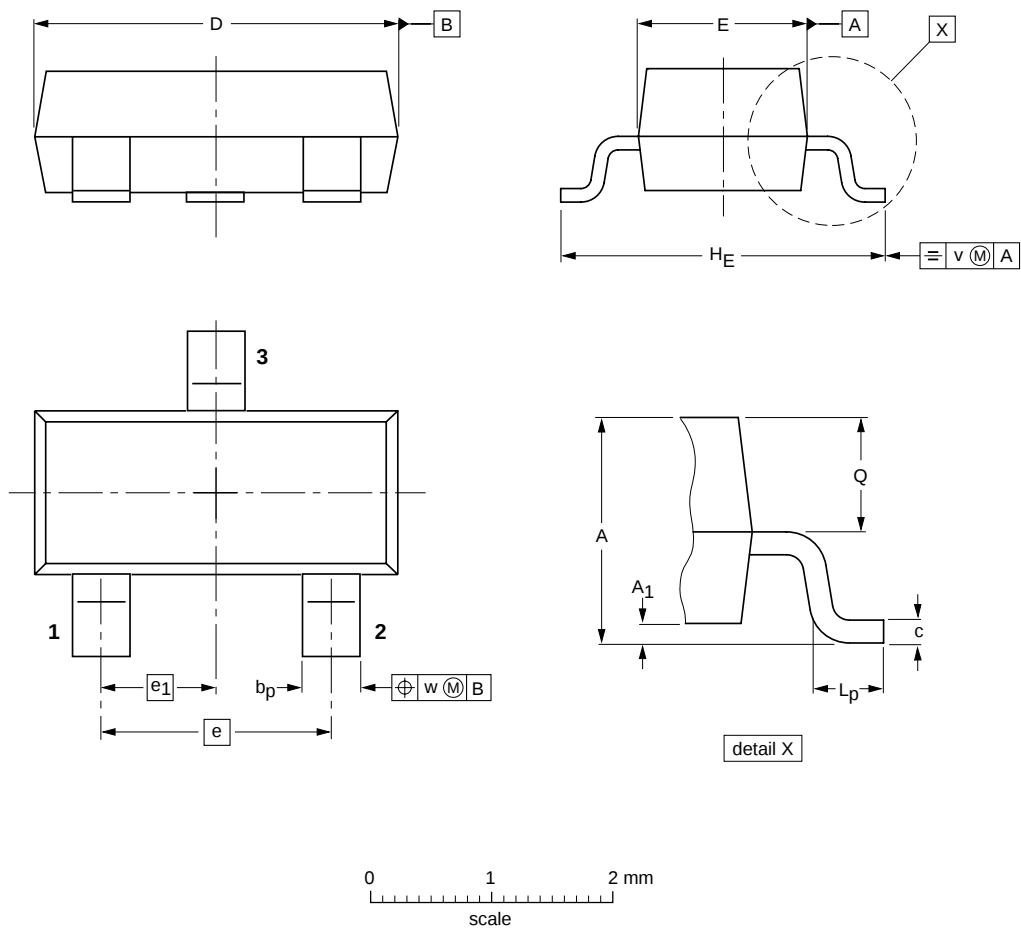
NPN medium frequency transistor

BF570

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16